

Notice of References Cited			Application No.	Applicant(s)		
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			Examiner Barbara Summers	Group Art Unit 2817		
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\* A copy of this reference is not being furnished with this Office action.  
(See Manual of Patent Examining Procedure, Section 707.05(a).)

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**LIST OF ART CITED BY APPLICANT**

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Attorney Docket No. CM03351J	Serial No. 09/828,431	Filing Date 4/9/01
Applicant: Kenneth D. Cornett	Group 2817	# 2

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**EXAMINER**Balava Summons**DATE CONSIDERED:**5/8/03

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*Barbara Summons*

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